

# [TS10T4]

## Nanoelectronic and Quantum Devices 4

<b>Date &amp; Time</b>	July 4(Thu.), 2024 / 14:00–15:30
<b>Place</b>	Room 206A
<b>Session Chair(s)</b>	Kyungmee Song (SAIT)

**TS10T4\_I\_1 \*Invited 14:00–14:30****Large Area Electronics based on 2D materials**

Jong-Hyun Ahn

*(Yonsei University)***TS10T4\_O\_2 14:30–14:45****Process Control of Novel Molybdenum Nitride Electrode for Enhanced Reliability of (Hf,Zr)O<sub>2</sub> Ferroelectric Thin Film**

Hyojun Choi, Kun Yang, Ju Yong Park, Sun Young Lee, Jaewook Lee, Dong In Han, and Min Hyuk Park

*(Seoul National University)***TS10T4\_O\_3 14:45–15:00****The Impact of Tin Doping on the Physical Characteristics of CdO Nanostructured Films**

Hassan Haruna, Abdurrahman Isa Hamza, and Murtala Ibrah

*(Kano State Polytechnic)***TS10T4\_O\_4 15:00–15:15****Bidirectional GeS-Based Threshold Switching Selector Device with High Uniformity for Integration in ReRAM Cross-Point Arrays**

Asif Ali, Haider Abbas, Li Jiayi, and Diing Shenp Ang

*(Nanyang Technological University)***TS10T4\_O\_5 15:15–15:30****Role of Oxide Barrier in NbO<sub>x</sub> Layer with Noninert Electrodes for High-Yield Threshold Switching Characteristics**

Hyeonsik Choi and Jiyong Woo

*(Kyungpook National University)*